High Power Laser Diode Chip

Part Number: CHP-248

High Power Chip
Single-Mode Fabry-Perot
CW Wavelength at 1310nm

Features

- High Output Power
- High Dynamic Range
- High Efficiency
- Standard Bare Die
- Cost Effective

Application

- Professional Medical
- FMCW LiDAR
- Datacom
- Data Centers
- OTDR

SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

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Specification

CHP-248

Optical	Symbol	Typ.	Units
Center Wavelength	λ_c	1310	nm (±20)
Output Power (CW)*	P_{out}	0.45	watts (±10%)
Chip Cavity Length	CL	2500	µm
Emitter Width	W	4	µm
Spectral Width FWHM	$\Delta\lambda$	15	nm
Slope Efficiency	η	0.5	W/A
Fast Axis Div.	$\Theta_{\perp}$	30	deg FWHM
Slow Axis Div.	$\Theta_{\parallel}$	13	deg FWHM
Electrical	**Symbol**		**Units**
Power Conversion Eff.	η	15	%
Threshold Current	I_{TH}	0.05	A
Operating Current	I_{op}	1	A
Operating Voltage	V_{op}	2.7	V
Mechanical		**Range**	**Units**
Operating Temp.**		-40 to 60	°C
Storage Temp.		-40 to 80	°C

*Specified values are rated at a constant heat sink temperature of 20°C.
**High temperature operation will reduce performance and MTTF.
Unless otherwise indicated all values are nominal.

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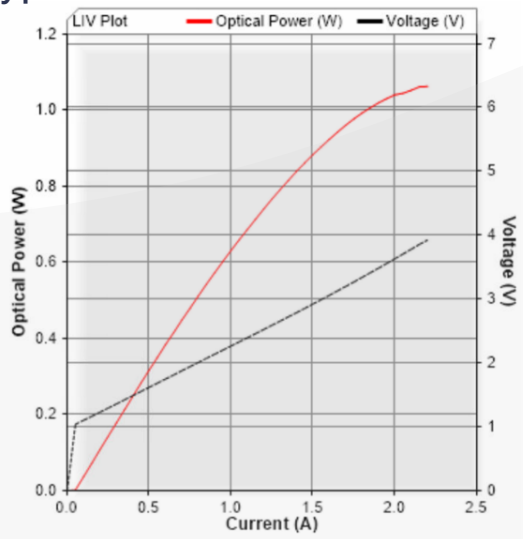
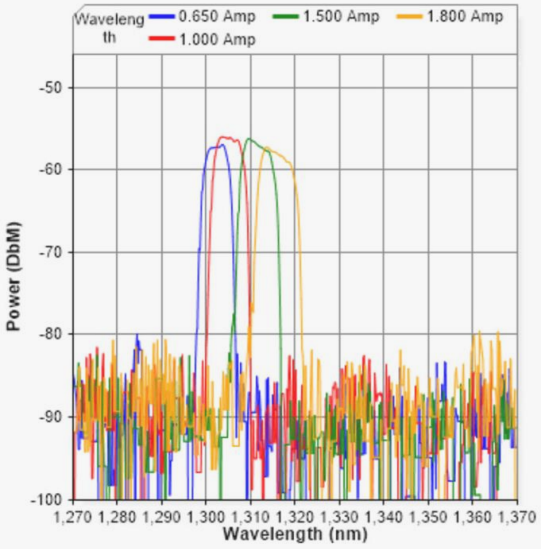
SemiNex Laser Diodes CHP-248

Graphs & Data

Typical CHP L-I-V Characteristics



Typical CHP Output Spectrum



*Graphs and Data were collected from mounted parts

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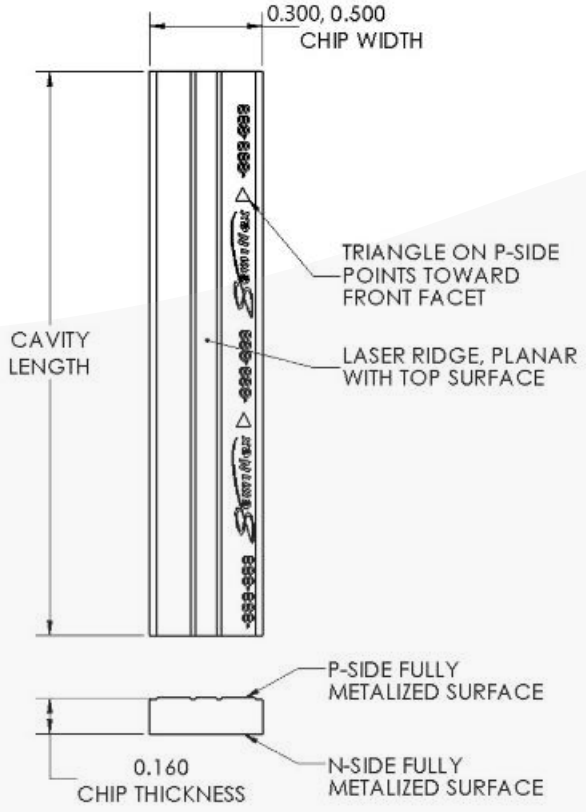
Mechanical Drawing



CHIP ATTRIBUTES

APERTURE WIDTH (µm)	Single Mode (4, 5) ± 1 Multi Mode (50, 95, 180, 350) ± 3
CHIP WIDTH (µm)	300, 500 ± 10
THICKNESS (µm)	160 ± 10
CAVITY LENGTH (µm)	Varies ± 10

P METALIZATION

MATERIAL	THICKNESS (nm)	TOLERANCE (nm)
Ti	50	± 10
Pt	125	± 25
Au	250	± 50

N METALIZATION

MATERIAL	THICKNESS (nm)	TOLERANCE (nm)
Ti	30	± 10
Pt	125	± 25
Au	400	± 40

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